IR-Lumineszenzdiode (850 nm) mit hoher Ausgangsleistung
High Power Infrared Emitter (850 nm)
Lead (Pb) Free Product - RoHS Compliant

SFH 4254

Vorläufige Daten / Preliminary Data

Wesentliche Merkmale

- Homogene Abstrahlung
- Typische Peakwellenlänge 850 nm
- Feuchte-Empfindlichkeitsstufe 2 nach JEDEDC Standard J-STD-020C

Features

- Homogenous Radiation Pattern
- Typical Peakwavelength 850 nm
- Moisture Sensitivity Level 2 according to JEDEDC Standard J-STD-020C

Anwendungen

- Schnelle Datenübertragung mit Übertragungsraten bis 100 Mbaud (IR Tastatur, Joystick, Multimedia)
- Analoge und digitale Hi-Fi Audio- und Videosignalübertragung
- Batteriebetriebene Geräte (geringe Stromaufnahme)
- Alarm- und Sicherungssysteme

Applications

- High data transmission rate up to 100 Mbaud (IR keyboard, Joystick, Multimedia)
- Analog and digital Hi-Fi audio and video signal transmission
- Low power consumption (battery) equipment
- Alarm and safety equipment

Sicherheitshinweise

Je nach Betriebsart emittieren diese Bauteile hochkonzentrierte, nicht sichtbare Infrarot-Strahlung, die gefährlich für das menschliche Auge sein kann. Produkte, die diese Bauteile enthalten, müssen gemäß den Sicherheits-richtlinien der IEC-Normen 60825-1 und 62471 behandelt werden.

Safety Advices

Depending on the mode of operation, these devices emit highly concentrated non visible infrared light which can be hazardous to the human eye. Products which incorporate these devices have to follow the safety precautions given in IEC 60825-1 and IEC 62471.

Typ **Type**	**Bestellnummer** **Ordering Code**	**Strahlstärkegruppierung**[1] (I_F = 50 mA, t_p = 20 ms) **Radiant intensity grouping**[1] I_e (mW/sr)
SFH 4254	Q65110A6462	>4 (typ. 7)

[1] gemessen bei einem Raumwinkel Ω = 0.01 sr / measured at a solid angle of Ω = 0.01 sr

ATTENTION - Observe Precautions For Handling - Electrostatic Sensitive Device

Grenzwerte (T_A = 25 °C)
Maximum Ratings

Bezeichnung **Parameter**	**Symbol** **Symbol**	**Wert** **Value**	**Einheit** **Unit**
Betriebs- und Lagertemperatur Operating and storage temperature range	T_{op}; T_{stg}	– 40 … + 100	°C
Sperrspannung Reverse voltage	V_R	5	V
Vorwärtsgleichstrom Forward current	I_F	70	mA
Stoßstrom Surge current	I_{FSM}	1	A
Leistungsaufnahme Power dissipation	P_{tot}	120	mW
Wärmewiderstand Sperrschicht - Umgebung bei Montage auf FR4 Platine, Padgröße je 5 mm² Thermal resistance junction - ambient mounted on PC-board (FR4), padsize 5 mm² each	R_{thJA}	530	K/W
Wärmewiderstand Sperrschicht - Lötstelle bei Montage auf Metall-Block Thermal resistance junction - soldering point, mounted on metal block	R_{thJS}	300	K/W

Kennwerte (T_A = 25 °C)
Characteristics

Bezeichnung **Parameter**	**Symbol** **Symbol**	**Wert** **Value**	**Einheit** **Unit**
Wellenlänge der Strahlung Wavelength at peak emission I_F = 100 mA	λ_{peak}	850	nm
Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} I_F = 100 mA	$\Delta\lambda$	35	nm
Abstrahlwinkel Half angle	φ	± 60	Grad deg.

Kennwerte (T_A = 25 °C)
Characteristics (cont'd)

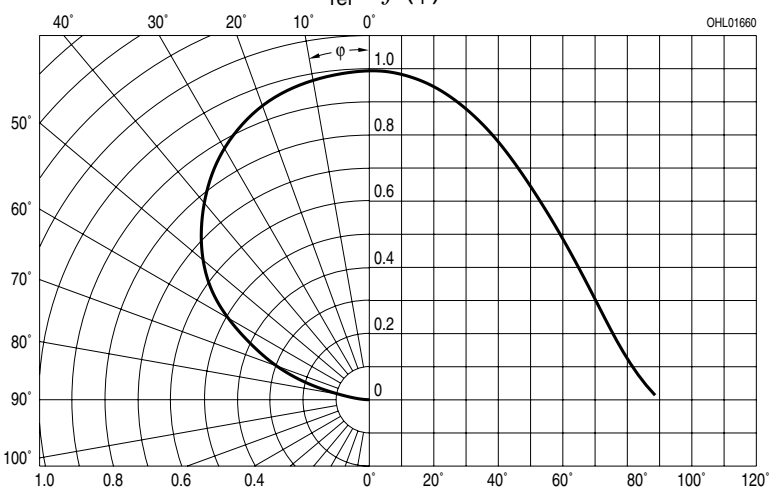
Bezeichnung **Parameter**	**Symbol** **Symbol**	**Wert** **Value**	**Einheit** **Unit**
Aktive Chipfläche Active chip area	A	0.09	mm^2
Abmessungen der aktiven Chipfläche Dimension of the active chip area	$L \times B$ $L \times W$	0.3 × 0.3	mm²
Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, bei I_F = 100 mA, R_L = 50 Ω Switching times, I_e from 10% to 90% and from 90% to 10%, I_F = 100 mA, R_L = 50 Ω	t_r, t_f	12	ns
Durchlassspannung Forward voltage I_F = 50 mA, t_p = 20 ms I_F = 1 A, t_p = 100 µs	 V_F V_F	 1.4 (< 1.7) 2.4 (< 3.0)	 V V
Sperrstrom Reverse current V_R = 5 V	I_R	not designed for reverse operation	µA
Gesamtstrahlungsfluss Total radiant flux I_F = 50 mA, t_p = 20 ms	$\Phi_{e\ typ}$	23	mW
Temperaturkoeffizient von I_e bzw. Φ_e, I_F = 100 mA Temperature coefficient of I_e or Φ_e, I_F = 100 mA	TC_I	– 0.5	%/K
Temperaturkoeffizient von V_F, I_F = 100 mA Temperature coefficient of V_F, I_F = 100 mA	TC_V	– 0.7	mV/K
Temperaturkoeffizient von λ, I_F = 100 mA Temperature coefficient of λ, I_F = 100 mA	TC_λ	+ 0.2	nm/K

Strahlstärke I_e in Achsrichtung[1)]
gemessen bei einem Raumwinkel Ω = 0.01 sr
Radiant Intensity I_e in Axial Direction
at a solid angle of Ω = 0.01 sr

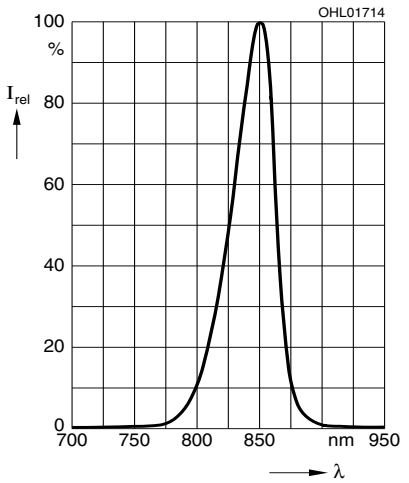
Bezeichnung Parameter	Symbol	Werte Values		Einheit Unit
		SFH 4254-P	SFH 4254-Q	
Strahlstärke Radiant intensity I_F = 50 mA, t_p = 20 ms	$I_{e\ min}$ $I_{e\ max}$	4 8	6.3 12.5	mW/sr mW/sr
Strahlstärke Radiant intensity I_F = 1 A, t_p = 100 µs	$I_{e\ typ}$	70	80	mW/sr

1) Nur eine Gruppe in einer Verpackungseinheit (Streuung kleiner 2:1) /
Only one group in one packing unit (variation lower 2:1)

Abstrahlcharakteristik
Radiation Characteristics $I_{rel} = f(\varphi)$

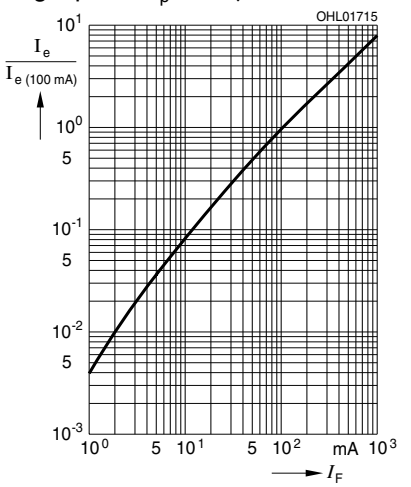


Relative Spectral Emission
$I_{rel} = f(\lambda)$

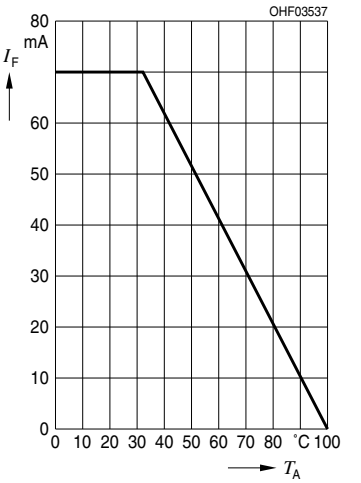


Radiant Intensity $\frac{I_e}{I_e\ 100\ mA} = f(I_F)$

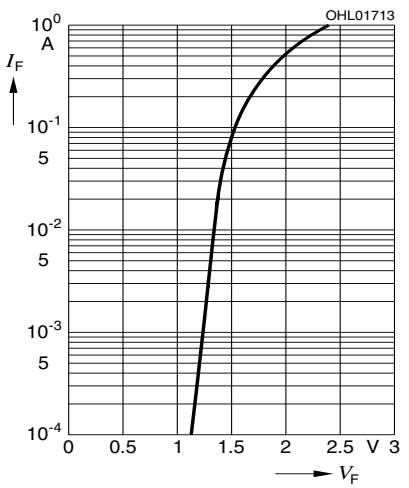
Single pulse, t_p = 20 µs



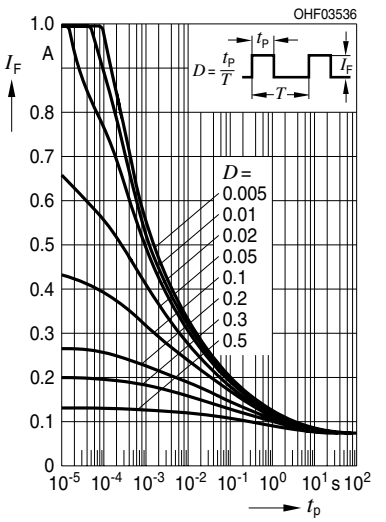
Max. Permissible Forward Current
$I_F = f(T_A)$, R_{thJA} = 530 K/W



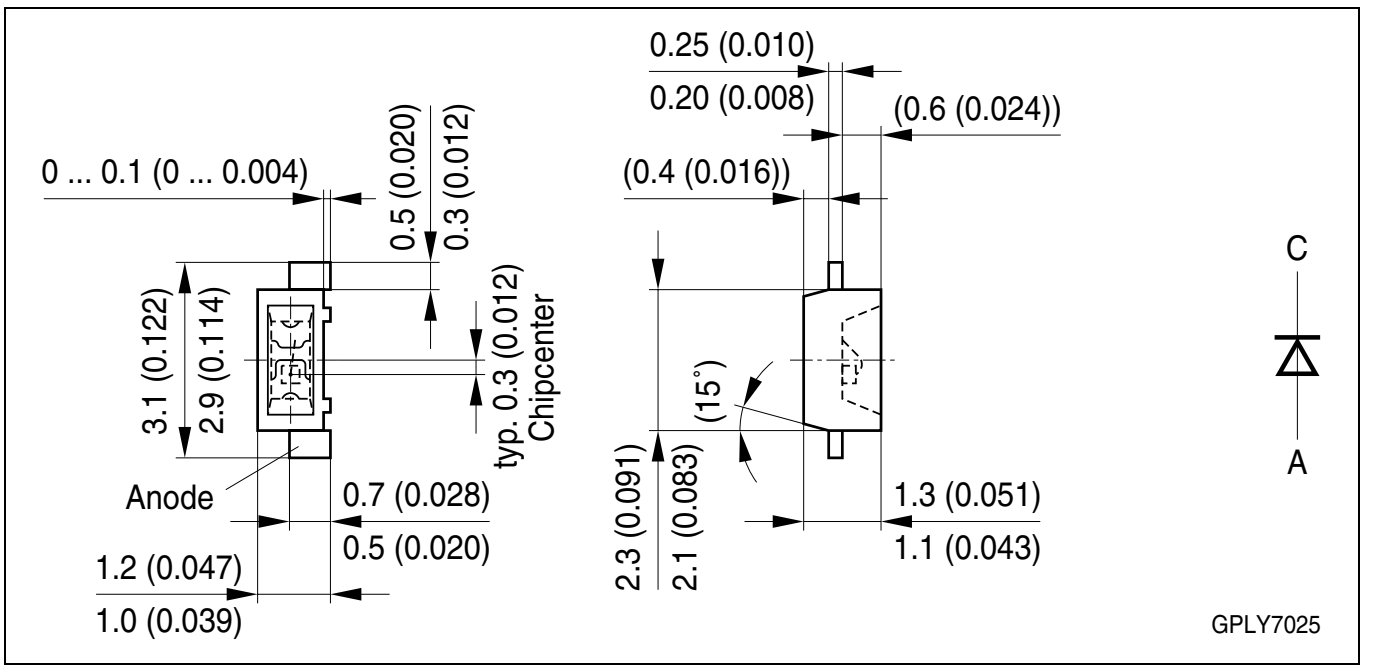
Forward Current $I_F = f(V_F)$
Single pulse, t_p = 20 µs



Permissible Pulse Handling Capability $I_F = f(\tau)$, T_A = 25 °C, duty cycle D = parameter



Maßzeichnung
Package Outlines



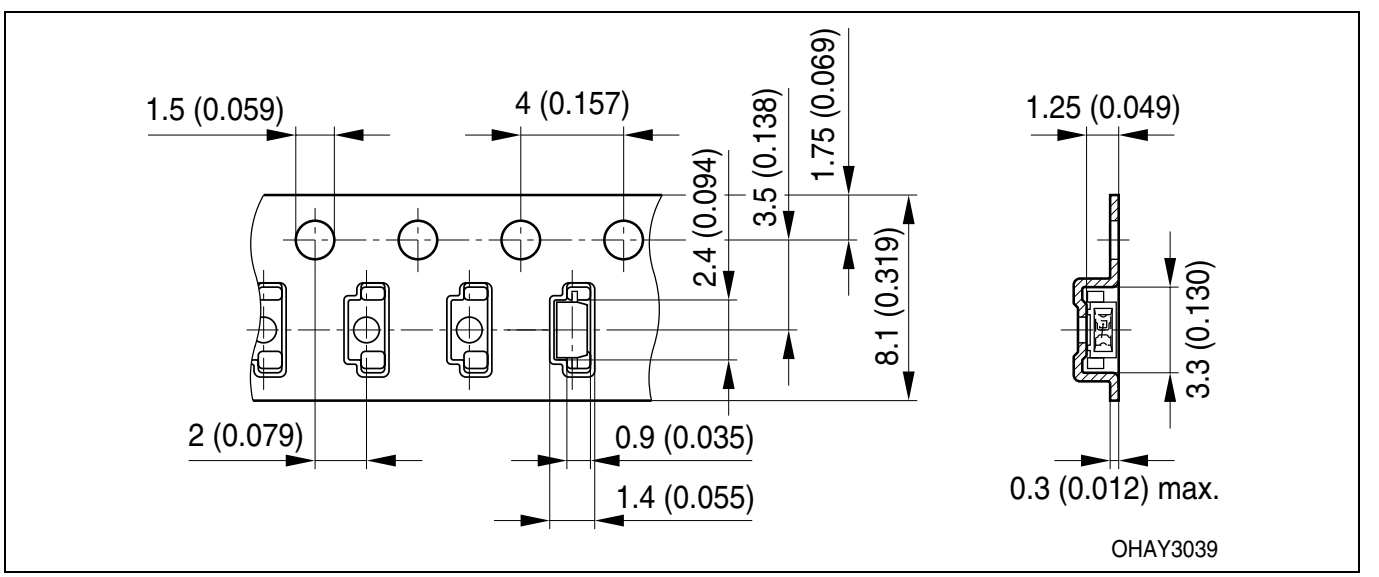
Maße in mm (inch) / Dimensions in mm (inch).

Gurtung / Polarität und Lage

Verpackungseinheit 3000/Rolle, ø180 mm
oder 10000/Rolle, ø330 mm

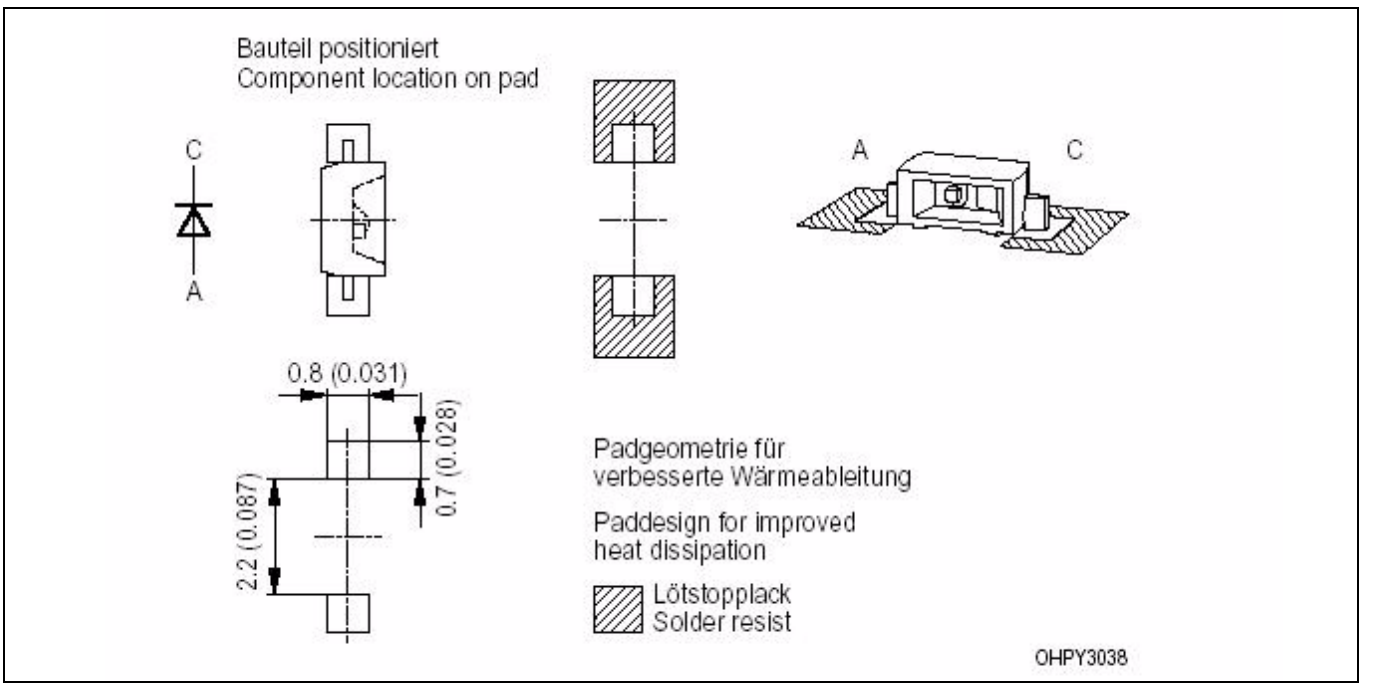
Method of Taping / Polarity and Orientation

Packing unit 3000/reel, ø180 mm
or 10000/reel, ø330 mm



Maße in mm (inch) / Dimensions in mm (inch).

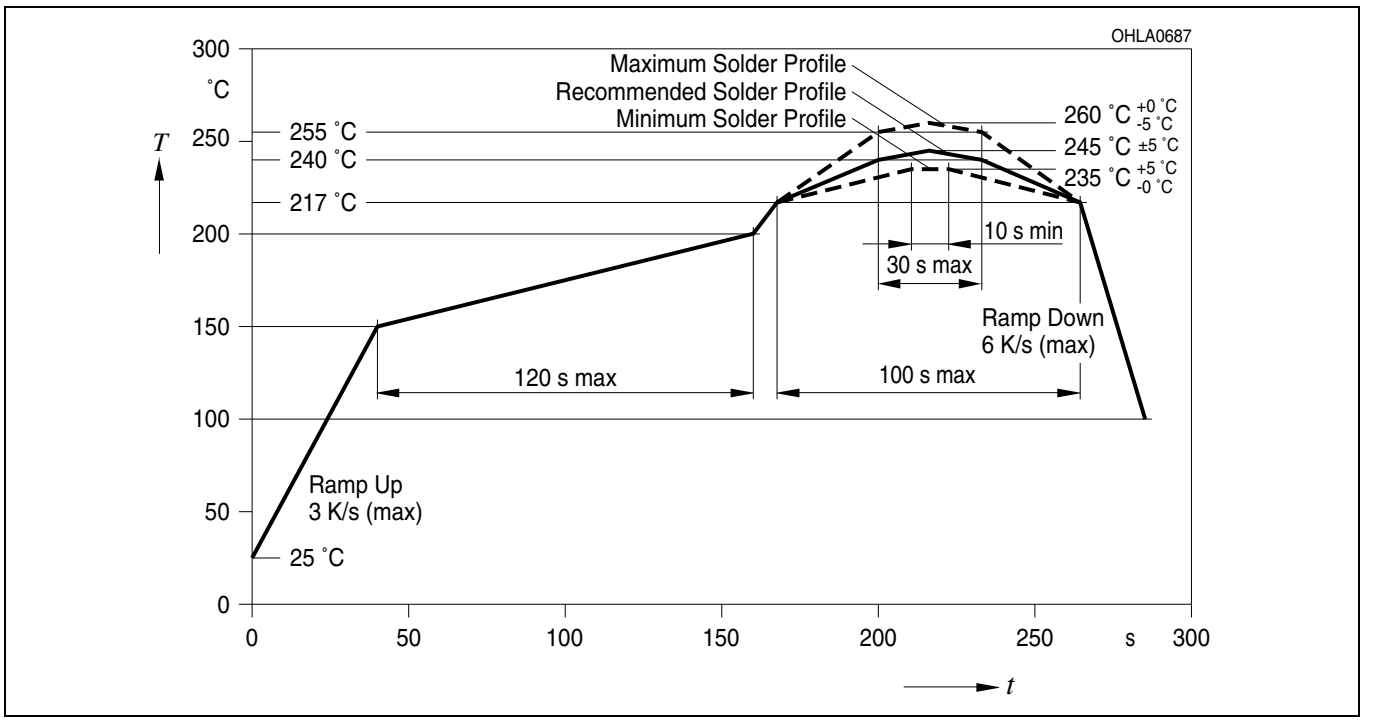
Empfohlenes Lötpaddesign
Recommended Solder Pad Design



Maße in mm (inch) / Dimensions in mm (inch).
Gehäuse hält TTW-Löthitze aus / Package able to withstand TTW-soldering heat.

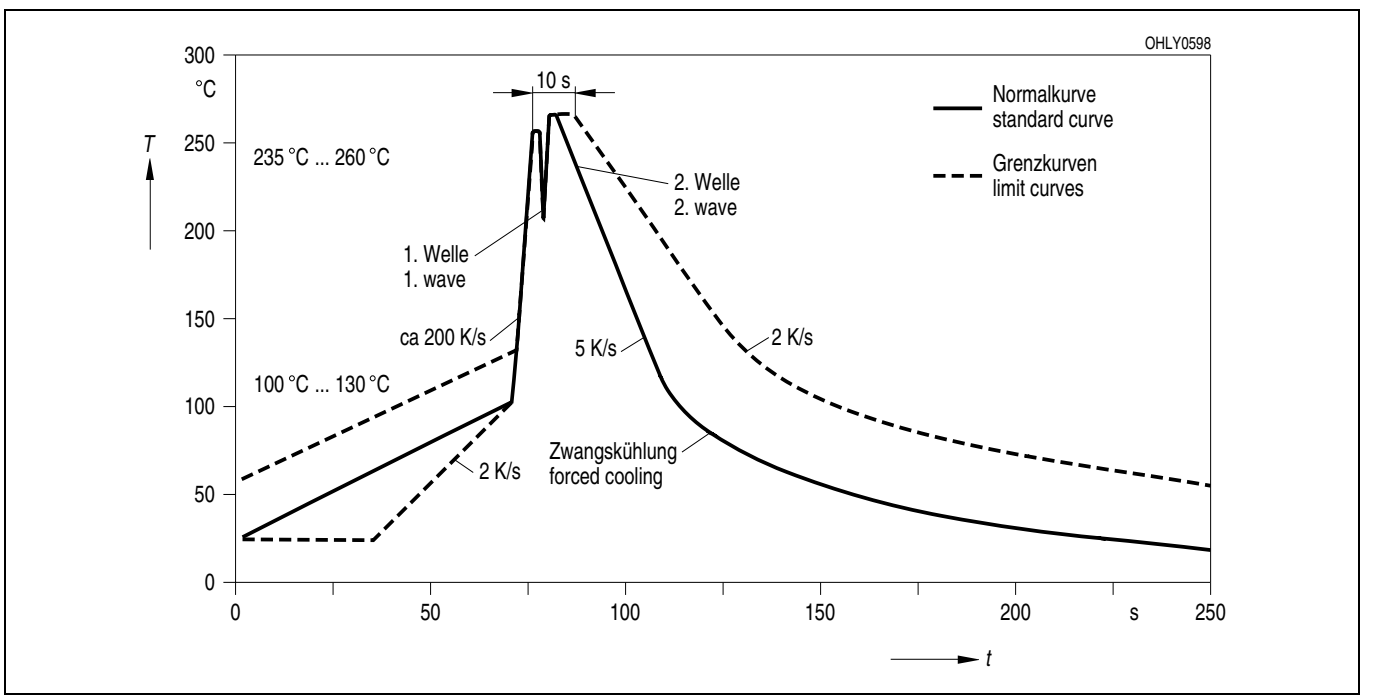
Lötbedingungen
Soldering Conditions
Reflow Lötprofil für bleifreies Löten
Reflow Soldering Profile for lead free soldering

Vorbehandlung nach JEDEC Level 2
Preconditioning acc. to JEDEC Level 2
(nach J-STD-020C)
(acc. to J-STD-020C)



Wellenlöten (TTW)
TTW Soldering

(nach CECC 00802)
(acc. to CECC 00802)



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按照中国的相关法规和标准，不含有毒有害物质或元素。

The information describes the type of component and shall not be considered as assured characteristics.
Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances. For information on the types in question please contact our Sales Organization.

Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

Components used in life-support devices or systems must be expressly authorized for such purpose! Critical components [1] , may only be used in life-support devices or systems [2] with the express written approval of OSRAM OS.

[1] A critical component is a component usedin a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.

[2] Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered.